

东莞市华远电子有限公司

DONG GUAN SHI HUA YUAN ELECTRON CO..LTD.

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TO-92 Plastic-Encapsulate Transistors

2SC2001

TRANSISTOR (NPN)

FEATURES

Power dissipation

 P_{CM} : 0.6 W (Tamb=25)

Collector current

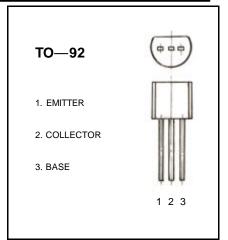
I_{CM} : 0.7 A

Collector-base voltage

 $V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

 T_J , T_{stg} : -55 to +150



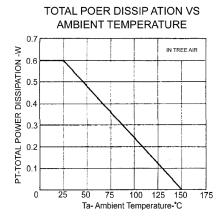
ELECTRICAL CHARACTERISTICS (Tamb=25

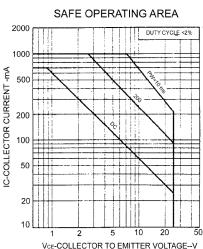
unless otherwise specified)

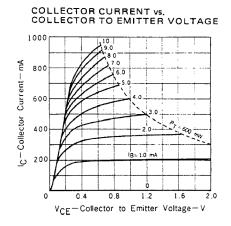
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	Ic=100μA , I _E =0	30		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA , I _B =0	25		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA , I _C =0	5		V
Collector cut-off current	I _{CBO}	V _{CB} =30 V , I _E =0		0.1	μΑ
Collector cut-off current	I _{CEO}	V _{CE} =20 V , I _B =0		0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =5 V , I _C =0		0.1	μΑ
DC current gain	h _{FE}	V _{CE} =1V, I _C =100m A	90	400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =700mA, I _B = 70mA		0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 700mA, I _B =70mA		1.2	V
Transition frequency	f _T	$V_{CE}=6V$, $I_{C}=10$ mA $f=30$ MHz	50		MHz

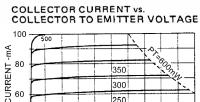
CLASSIFICATION OF h_{FE}

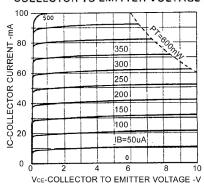
Rank	M	L	К
Range	90-180	135-270	200-400

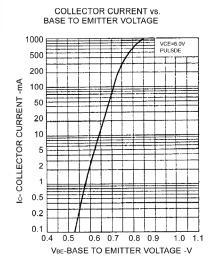


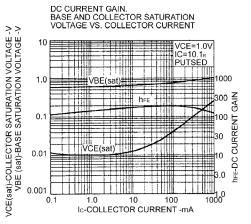


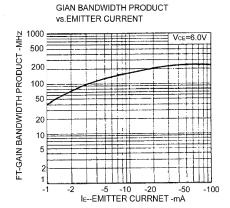












TO-92 PACKAGE OUTLINE DIMENSIONS





Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.400	4.700	0.173	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.270TYP		0.050TYP		
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ö		1.600		0.063	
$\overline{}$	0.000	0.380	0.000	0.015	